

2SK1103

Silicon N-Channel Junction FET

For switching

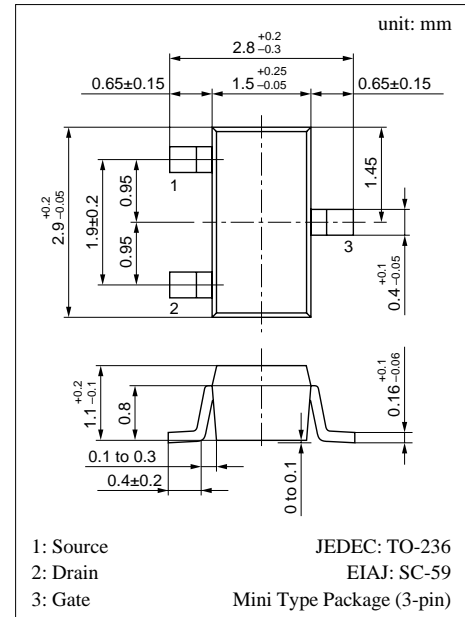
Complementary to 2SJ163

■ Features

- Low ON-resistance
- Low-noise characteristics

■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Gate to Drain voltage	V _{GDS}	-65	V
Drain current	I _D	20	mA
Gate current	I _G	10	mA
Allowable power dissipation	P _D	150	mW
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C



Marking Symbol (Example): 4L

■ Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I _{DSS} *	V _{DS} = 10V, V _{GS} = 0	0.2		6	mA
Gate to Source leakage current	I _{GSS}	V _{GS} = -30V, V _{DS} = 0			-10	nA
Gate to Drain voltage	V _{GDS}	I _G = -10μA, V _{DS} = 0	-65			V
Gate to Source cut-off voltage	V _{GSC}	V _{DS} = 10V, I _D = 10μA		-1.5	-3.5	V
Forward transfer admittance	Y _{fs}	V _{DS} = 10V, I _D = 1mA, f = 1kHz	1.8	2.5		mS
Drain to Source ON-resistance	R _{DS(on)}	V _{DS} = 10mV, V _{GS} = 0		300		Ω
Input capacitance (Common Source)	C _{iss}	V _{DS} = 10V, V _{GS} = 0, f = 1MHz		7		pF
Reverse transfer capacitance (Common Source)	C _{rss}			1.5		pF

* I_{DSS} rank classification

Runk	O	P	Q	R
I _{DSS} (mA)	0.2 to 1	0.6 to 1.5	1 to 3	2.5 to 6
Marking Symbol	4LO	4LP	4LQ	4LR

